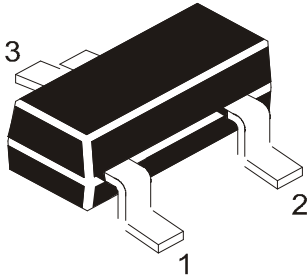


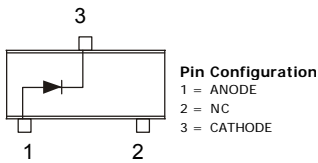
SILICON PLANAR SCHOTTKY DIODES

**BAR43, BAR43A
BAR43C, BAR43S**

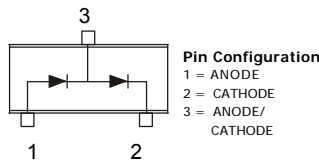
**SOT-23
Formed SMD Package**



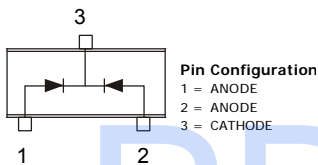
BAR43



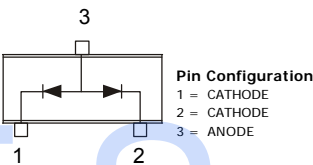
BAR43S



BAR43C



BAR43A



BAR43= D95
BAR43A=DB1
BAR43C=DB2
BAR43S=DA5

General Purpose, metal to Silicon Diodes Featuring Very Low Turn-on Voltage and Fast Switching

ABSOLUTE MAXIMUM RATINGS (see note 1)

DESCRIPTION	SYMBOL	VALUE	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Forward Current	I_F	100	mA
Repetitive Peak Forward Current	I_{FRM}	350	mA
Surge Non Repetitive Forward Current	I_{FSM}	750	mA
Power Dissipation $T_a=25^\circ\text{C}$ (see note 2)	$*P_D$	160	mW
Storage Temperature Range	T_{stg}	- 55 to +150	$^\circ\text{C}$
Junction Temperature	T_j	125	$^\circ\text{C}$

THERMAL RESISTANCE (see note 3)

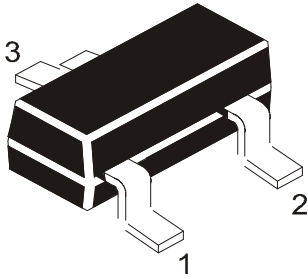
Junction to Ambient in free air	$*R_{th(j-a)}$	625	$^\circ\text{C/W}$
Junction to Substrate	$R_{th(j-SR)}$	400	$^\circ\text{C/W}$

*Mounted on a ceramic substrate: 7 x 5 x 0.5mm

Note:- 1 For double diodes maximum ratings apply to each diode, provided that rated P_D is not exceeded
2 For double diodes P_D is the total power dissipation of the two diodes
3 For double diodes R_{th} refer to the total power dissipation in the two diodes and is given independently of the power distribution in the two diodes

SILICON PLANAR SCHOTTKY DIODES

BAR43, BAR43A
BAR43C, BAR43S



SOT-23
Formed SMD Package

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless specified otherwise)

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Reverse Breakdown Voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	30		V
Forward Voltage	V_F	$I_F=2\text{mA}$	0.26	0.33	V
		$I_F=15\text{mA}$		0.45	V
		$I_F=100\text{mA}$		1.00	V
Reverse Current	I_R	$V_R=25\text{V}$		500	nA
		$V_R=25\text{V}, T_a=100^\circ\text{C}$		100	μA

DYNAMIC CHARACTERISTICS

DESCRIPTION	SYMBOL	TEST CONDITION	MIN	MAX	UNIT
Diode Capacitance	C	$V_R=1\text{V}, f=1\text{MHz}$	TYP 7		pF
Reverse Recovery Time When Switched From	t_{rr}	$I_F=10\text{mA}$, to $I_R=10\text{mA}$, $I_{RR}=1\text{mA}, R_L=100\Omega$		5	ns

BAR43_A_C_S Rev300403E

Disclaimer

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